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(54) Title: METHOD OF VIA FILLING

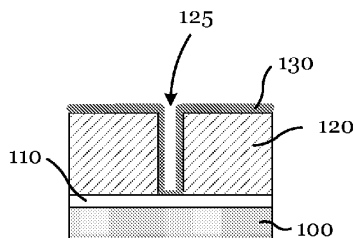


FIG. 1B

(57) Abstract: A method of processing a substrate includes exposing the substrate to a boron-containing precursor to adsorb over the substrate, where the substrate includes a dielectric layer formed over a conductive layer, and the conductive layer is exposed at a bottom of a recess formed in the dielectric layer. The method includes exposing the adsorbed boron-containing precursor to a plasma and filling the recess with a conductive fill material bottom up by a vapor deposition process, where a vertical deposition rate of the conductive fill material is greater than a lateral deposition rate of the conductive fill material.

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